



100V 175°C PNP LOW SAT HIGH POWER TRANSISTOR IN POWERDI5060-8

Features

- BV_{CEO} > -100V
- I_C = -3A Continuous Collector Current
- I_{CM} = -8A Peak Pulse Current
- $R_{CE(SAT)} = 110m\Omega$ (typ)
- Rated to +175°C—Ideal for High Ambient Temperature Environments
- Complementary Part DXTN3C100PS
- Meets Requirements of Automotive Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

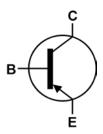
- Case: Power®DI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.097 grams (Approximate)

Applications

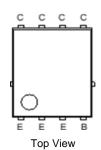
- Power Management
- Load Switch
- Linear Mode Voltage Regulator
- Backlighting Applications







Internal Schematic



Pin Configuration

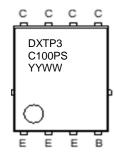
Ordering Information

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTP3C100PSQ-13	Automotive	DXTP3C100PS	13	12	2500

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

Marking Information



DXTP3 = Product Type Marking Code C100PS = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Base Current	I _B	-0.5	A
Continuous Collector Current	Ic	-3	А
Peak Pulse Collector Current	I _{CM}	-8	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	P _D	5	W	
Thermal Decistance, Junetian to Ambient	(Note 5)	Б	40	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\Theta JA}$	120		
Thermal Decistance, Junetica to Cons	(Note 5, 7)	Б	2	0000	
Thermal Resistance, Junction to Case	(Note 6, 7)	R _{eJC}	12	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	V0008	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400V	V	С

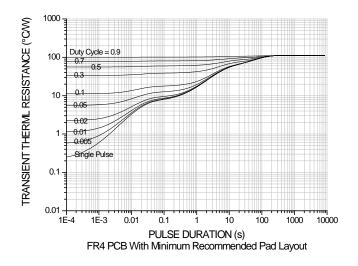
Notes:

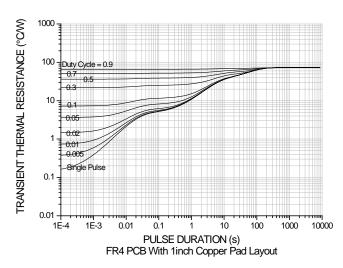
- 5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper, on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions while operating in a steady state.

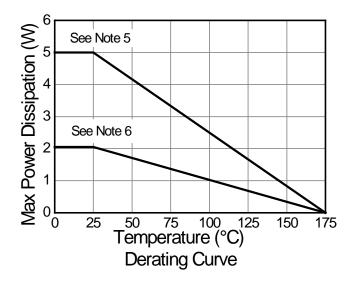
 6. Same as Note 5 except mounted on minimum recommended pad layout.
- 7. Thermal resistance from junction to the top of the case.
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Typical Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)









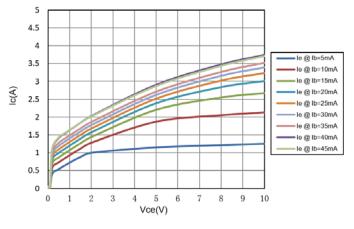
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

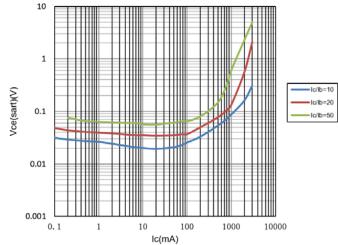
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-100	_	_	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-100	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA
Collector-Base Cutoff Current		_	_	-100	nA	V _{CB} = -80V
Collector-Base Cuton Current	I _{CBO}	_	_	-50	μA	V _{CB} = -80V @Tj = 150°C
Emitter Cutoff Current	I _{EBO}	_	_	-100	nA	V _{EB} = -7V
Collector-Emitter Cutoff Current	I _{CES}	_	_	-100	nA	V _{CES} = -80V
ON CHARACTERISTICS (Note 9)						
		170	305	_		I _C = -500mA, V _{CE} = -10V
DC Current Gain	h	160	275	_		I _C = -1A, V _{CE} = -10V
DC Curient Gain	h _{FE}	45	90	_	_	I _C = -2A, V _{CE} = -10V
		10	20	_		I _C = -3A, V _{CE} = -10V
Collector-Emitter Saturation Voltage	V	_	-70	-110	mV	$I_C = -0.5A, I_B = -50mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-220	-360		I _C = -2A, I _B = -200mA
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	110	180	mΩ	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	-0.91	-1	V	$I_C = -1A$, $I_B = -50mA$
Base-Emilier Saturation voitage		_	-1.02	-1.2		$I_C = -2A$, $I_B = -200mA$
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	-0.68	-0.9	V	$I_C = -0.1A, V_{CE} = -2V$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	_	125	_	MHz	V _{CE} = -10V, I _C = -100mA, f = 100MHz
Output Capacitance	C _{obo}	_	30	_	pF	V _{CB} = -10V, f = -1MHz
Delay Time	t _d	_	20	_	ns	
Rise Time	t _r	_	180	_	ns	
Turn-On Time	t _(on)	_	200	_	ns	$V_{CC} = -12.5V, I_{C} = -1A$
Storage Time	ts	_	350	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$
Fall Time	t _f	_	220	_	ns	
Turn-Off Time	t _(off)	_	570		ns	

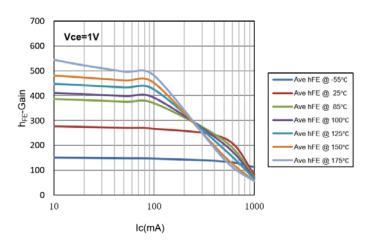
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

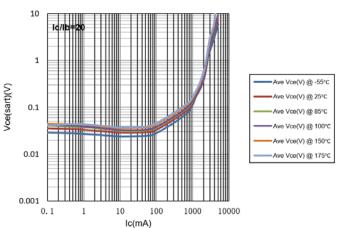


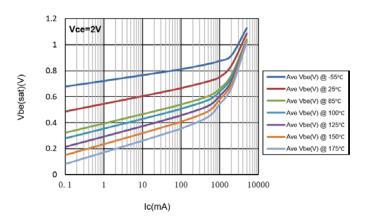
Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

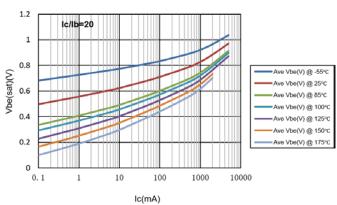














Package Outline Dimensions

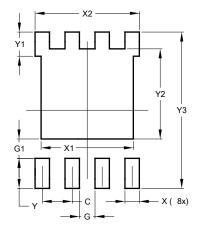
Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0	0.05	_		
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF			
С	0.230	0.330	0.277		
D	5	.15 BS0			
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
Е	6.40 BSC				
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1.27BSC				
k	1.05	_	_		
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
M	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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